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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/811,973	03/30/2004	Toshiya Nozawa	843.43729X00	2994
20457	7590	08/11/2005	EXAMINER	
ANTONELLI, TERRY, STOUT & KRAUS, LLP 1300 NORTH SEVENTEENTH STREET SUITE 1800 ARLINGTON, VA 22209-3873				SANDVIK, BENJAMIN P
ART UNIT		PAPER NUMBER		
2826				

DATE MAILED: 08/11/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/811,973	NOZAWA ET AL.	
	Examiner Ben P. Sandvik	Art Unit 2826	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) Responsive to communication(s) filed on ____.
- 2a) This action is FINAL. 2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) Claim(s) 1-20 is/are pending in the application.
- 4a) Of the above claim(s) ____ is/are withdrawn from consideration.
- 5) Claim(s) ____ is/are allowed.
- 6) Claim(s) 1-20 is/are rejected.
- 7) Claim(s) ____ is/are objected to.
- 8) Claim(s) ____ are subject to restriction and/or election requirement.

Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on ____ is/are: a) accepted or b) objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
 - a) All b) Some * c) None of:
 1. Certified copies of the priority documents have been received.
 2. Certified copies of the priority documents have been received in Application No. ____.
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|--|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. ____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date ____ | 6) <input type="checkbox"/> Other: ____ |

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1, 2, 6-8, 10-13, 16, and 17 are rejected under 35 U.S.C. 102(b) as being anticipated by Ochi et al (U.S. Patent #6344790).

With respect to **claim 1**, Ochi teaches first and second electrodes having layers containing copper as main components (Fig. 4, 3A and 3B); a semiconductor element arranged between said first and second electrodes and electrically connected to said first and second electrodes (Fig. 4, 2); and a glass sealing member which seals said first electrode, said semiconductor element, and said second electrode (Fig. 4, 1); wherein, in the first and second electrodes, ratios of the layers containing copper as main components are not less than 20 wt% (Fig. 2, 12).

With respect to **claim 2**, Ochi teaches that said first and second electrodes are constituted by Dumet wires (Col 1 Ln 26).

With respect to **claim 6**, Ochi teaches a glass material (potassium oxide, Col 3 Ln 40) that has a glass softening point of 560° C or less.

With respect to **claim 7**, Ochi teaches a glass material (silicon dioxide, Col 3 Ln 40) that has a sealing temperature of not 630° C or less.

With respect to **claim 8**, Ochi teaches a glass material (silicon dioxide, Col 3 Ln 40) that has a sealing temperature of not 630° C or less.

With respect to **claim 10**, Ochi teaches first and second electrodes wherein the ratios said layers containing copper as main components fall within the range of 20 to 25 wt% (Col 1 Ln 26).

With respect to **claim 11**, Ochi teaches first and second electrodes wherein the ratios said layers containing copper as main components fall within the range of 21 to 24 wt% (Col 1 Ln 26).

With respect to **claim 12**, Ochi teaches that said first and second electrodes have core portions (Fig. 2, 11) and said layers containing copper as main components, said layers being formed on the outer peripheries of said core portions (Fig. 2, 13).

With respect to **claim 13**, Ochi teaches that said core portions of said first and second electrodes comprise a nickel-containing alloy (Col 1 Ln 32).

With respect to **claim 16**, Ochi teaches that said core portions of said first and second electrodes are comprised of an alloy containing iron and nickel as main components (Col 1 Ln 32).

With respect to **claim 17**, Ochi teaches that said first and second electrodes have copper oxide layers formed on the outer peripheries of said layers containing copper as main components (Fig. 2, 13 and Col 1 Ln 33-34).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 3, 5, 9, 14, and 15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ochi, in view of Robinson et al (U.S. Patent #4042951).

With respect to **claim 3**, Ochi teaches all of the limitations of claim 1, but does not teach that said semiconductor element is a diode. Robinson teaches a semiconductor device that is a diode (Col 1 Ln 53-56). It would have been obvious to one of ordinary skill in the art at the time the invention was made to provide the device of Ochi with a diode as taught by Robinson in order to adapt the device to diode functions.

With respect to **claim 5**, Ochi teaches all of the limitations of claim 1, but does not teach that the semiconductor element has a metal electrode, wherein a sealing temperature of said glass sealing member is a temperature at which silicification of said metal electrode of the semiconductor element is not enhanced. Robinson teaches a semiconductor element with a metal electrode (Fig. 1, 15); and a sealing temperature of the glass sealing member (Col 3 Ln 17-20) is a temperature at which silicification of said metal electrode is not

enhanced. It would have been obvious to one of ordinary skill in the art at the time the invention was made to provide the device of Ochi with a semiconductor element having a metal electrode in order to make a reliable connection to the Dumet electrode, and to seal the glass member at a temperature at which silicification of said metal electrode is not enhanced in order to maintain the desired characteristics of the device.

With respect to **claim 9**, Ochi teaches all of the limitations of claim 1, but does not teach that the semiconductor element has a bump electrode; wherein the thickness of said layers containing copper as main components are larger than said thickness of said bump electrode. Robinson teaches a semiconductor element having a bump electrode (Fig. 1, 15), the thickness of copper containing layers being larger than the thickness of the bump electrode (Fig. 2, 31 and 32). It would have been obvious to one of ordinary skill in the art at the time the invention was made to make the device of Ochi with a semiconductor element having a bump electrode in order to improve the reliability of the connection to the Dumet electrode, and to make the thickness of the copper containing layers larger than the thickness of the bump electrode in order to maintain a small size of the package.

With respect to **claim 14**, Ochi teaches all of the limitations of claim 12, but does not teach that the nickel-containing alloy has a nickel content of 45 wt% or less. Robinson teaches a core portion comprised of a nickel-containing alloy having a nickel content of 45 wt% or less (Col 2 Ln 23-24). It would have been

obvious to one of ordinary skill in the art at the time the invention was made to produce the core portion of Ochi with a nickel content of 45 wt% or less as taught by Robinson in order to control the resistance of the electrode.

With respect to **claim 15**, Ochi teaches all of the limitations of claim 12, but does not teach that the nickel-containing alloy has a nickel content of 41-43 wt% or less. Robinson teaches a core portion comprised of a nickel-containing alloy having a nickel content of 41-43 wt% or less (Col 2 Ln 23-24). It would have been obvious to one of ordinary skill in the art at the time the invention was made to produce the core portion of Ochi with a nickel content of 41-43 wt% or less as taught by Robinson in order to control the resistance of the electrode.

Claim 18 is rejected under 35 U.S.C. 103(a) as being unpatentable over Ochi in view of Inazawa et al (U.S. Patent #5372886).

With respect to **claim 18**, Ochi teaches all of the limitations of claim 17, but does not teach that the thickness of the copper oxide layers are 1.5 micrometers or less. Inazawa teaches a wire that is provided with a copper oxide layer that is 1 micrometer thick (Col 8 Ln 19-21). It would have been obvious to one of ordinary skill in the art at the time the invention was made to provide the wire electrode of Ochi with a copper oxide layer with a thickness of less than 1.5 micrometers as taught by Inazawa in order to improve the insulation of the wire.

Claims 19 and 20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ochi, in view of Einthoven (U.S. Patent #4742377).

With respect to **claims 19 and 20**, Ochi teaches all of the limitations of claim 1, but does not teach that said semiconductor element comprises by a Schottky barrier diode having: a semiconductor substrate; an epitaxial layer formed on the semiconductor substrate; and a metal electrode formed on the epitaxial layer. Einthoven teaches a semiconductor element comprising a Schottky barrier diode (abstract) having: a semiconductor substrate (Fig. 4, 11); an epitaxial layer formed on the semiconductor substrate (Fig. 4, 5); and a metal electrode formed on the epitaxial layer (Fig. 4, 13, 15, 17) having a tungsten film (Col 3 Ln 4). It would have been obvious to one of ordinary skill in the art at the time the invention was made to provide the device of Ochi with a semiconductor device comprising a Schottky barrier diode as taught by Einthoven in order to use the device as a rectifier.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ben P. Sandvik whose telephone number is (571) 272-8446. The examiner can normally be reached on Mon-Fri.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Art Unit: 2826

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

bps

DEPT
EXAMINER

Evan PERT
EVAN PERT
PRIMARY EXAMINER